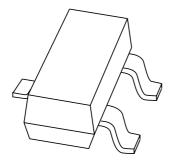
DISCRETE SEMICONDUCTORS

DATA SHEET



PMBD353 Schottky barrier double diode

Product specification Supersedes data of 1999 May 25 2001 Oct 15





Schottky barrier double diode

PMBD353

FEATURES

- Low forward voltage
- Small SMD package
- · Low capacitance.

APPLICATIONS

- UHF mixer
- · Sampling circuits
- Modulators
- Phase detection.

DESCRIPTION

Planar Schottky barrier double diode in a SOT23 small plastic SMD package.

MARKING

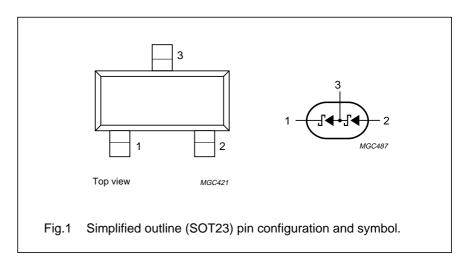
| TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|--------------------------------|
| PMBD353 | *4F |

Note

- 1. * = p: Made in Hong Kong.* = t: Made in Malaysia.
 - * = W: Made in China.

PINNING

| PIN | DESCRIPTION | | | | |
|-----|---|--|--|--|--|
| 1 | cathode k ₁ | | | | |
| 2 | anode a ₂ | | | | |
| 3 | common connection a ₁ , k ₂ | | | | |



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | MIN. | MAX. | UNIT | | |
|------------------|------------------------------------|------|------|------|--|--|
| Per diode | | | | | | |
| V _R | continuous reverse voltage – 4 V | | | | | |
| I _F | continuous forward current – 30 m/ | | | | | |
| T _{stg} | storage temperature | +150 | °C | | | |
| Tj | junction temperature – 100 °C | | | | | |

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ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

| SYMBOL | PARAMETER | CONDITIONS | MAX. | UNIT |
|----------------|-------------------|--|------|------|
| Per diode | | | | |
| V _F | forward voltage | see Fig.2 | | |
| | | I _F = 0.1 mA | 350 | mV |
| | | I _F = 1 mA | 450 | mV |
| | | I _F = 10 mA | 600 | mV |
| I _R | reverse current | V _R = 3 V; note 1; see Fig.3 | 0.25 | μΑ |
| C _d | diode capacitance | f = 1 MHz; V _R = 0; see Fig.4 | 1 | pF |

Note

1. Pulse test: t_p = 300 μ s; δ = 0.02.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|---------------------|---|------------|-------|------|
| R _{th j-a} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

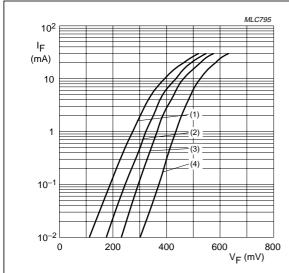
Note

1. Refer to SOT23 standard mounting conditions.

Schottky barrier double diode

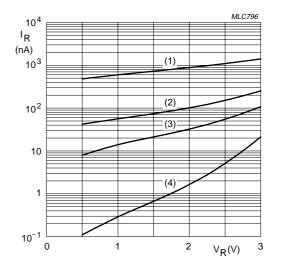
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GRAPHICAL DATA



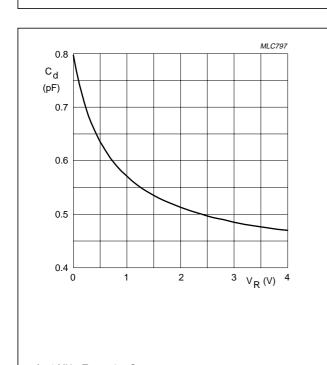
- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \,^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.2 Forward current as a function of forward voltage; typical values.



- (1) $T_{amb} = 100 \, ^{\circ}C$.
- (2) $T_{amb} = 60 \, ^{\circ}C$.
- (3) $T_{amb} = 25 \, ^{\circ}C$.
- (4) $T_{amb} = -40 \, ^{\circ}C$.

Fig.3 Reverse current as a function of reverse voltage; typical values.



f = 1 MHz; T_{amb} = 25 °C.

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

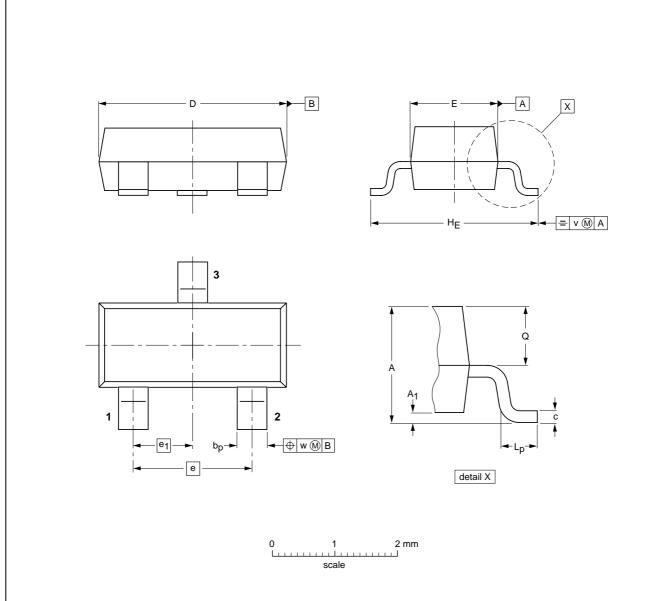
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



| DIMENSIONS | (mm are | the original | dimensions) |
|------------|---------|--------------|-------------|
|------------|---------|--------------|-------------|

| UNIT | Α | A ₁ max. | bp | С | D | E | е | e ₁ | HE | L _p | Q | v | w |
|------|------------|------------------------|--------------|--------------|------------|------------|-----|----------------|------------|----------------|--------------|-----|-----|
| mm | 1.1 0.9 | 0.1 | 0.48 0.38 | 0.15 0.09 | 3.0 2.8 | 1.4 1.2 | 1.9 | 0.95 | 2.5 2.1 | 0.45 0.15 | 0.55 0.45 | 0.2 | 0.1 |

| OUTLIN | IE | | REFER | EUROPEAN | ISSUE DATE | | |
|--------|----|-----|----------|----------|------------|------------|---------------------------------|
| VERSIO | N | IEC | JEDEC | EIAJ | | PROJECTION | ISSUE DATE |
| SOT23 | 3 | | TO-236AB | | | | 97-02-28 99-09-13 |

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DATA SHEET STATUS

| DATA SHEET STATUS(1) | PRODUCT STATUS ⁽²⁾ | DEFINITIONS |
|----------------------|----------------------------------|--|
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| Preliminary data | Qualification | This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product. |
| Product data | Production | This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Changes will be communicated according to the Customer Product/Process Change Notification (CPCN) procedure SNW-SQ-650A. |

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NOTES

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Contact information

For additional information please visit http://www.semiconductors.philips.com. Fax: +31 40 27 24825 For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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